

# Operational Amplifier, 36 V, 3 MHz, 0.95 mV Input Offset Voltage, Rail-to-Rail

## NCS20231, NCV20231, NCS20232, NCV20232, NCS20234, NCV20234

The NCS2023x series of op amps feature a wide supply range of 2.7 V to 36 V with an input offset voltage as low as  $\pm 0.95$  mV max. These op amps are available in single, dual, and quad channel configurations. Automotive qualified options are available under the NCV prefix with an optional extended operating temperature range from  $-40^{\circ}$ C to  $150^{\circ}$ C. All other versions are specified over the operating temperature range from  $-40^{\circ}$ C to  $125^{\circ}$ C.

#### **Features**

• Supply Voltage Range: 2.7 V to 36 V

• Temperature Range: -40°C to 150°C

• Unity Gain Bandwidth: 3 MHz

• Input Offset Voltage:  $\pm 1.2 \text{ mV max}$ ,  $T_A = -40 \text{ to } 150^{\circ}\text{C}$ 

• Input Offset Voltage Drift: ±2 μV/°C max

• Common-Mode Input Voltage Range

• Optimal:  $V_{SS} - 0.1$  to  $V_{DD} - 2 V$ 

• Functional:  $V_{SS} - 0.1$  to  $V_{DD} + 0.1$  V

 NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable

 These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### **Applications**

- Telecom Equipment
- Power Supply Designs
- Diesel Injection Control
- Automotive
- Motor Control



SC-88A / SC70-5 CASE 419A-02



TSOP-5 CASE 483



SOT-553, 5 LEAD CASE 463B



UDFN8 CASE 517AW



SOIC-14 NB CASE 751A-03



SOIC-8 NB CASE 751-07



#### **DEVICE MARKING INFORMATION**

See general marking information in the device marking section on page 2 of this data sheet.

#### **PIN CONNECTIONS**

See pin connections on page 3 of this data sheet.

#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 2 of this data sheet

#### **DEVICE MARKING INFORMATION**



TSOP-5 CASE 483



SC-88A / SC70-5 CASE 419A-02



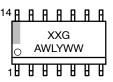
SOT-553, 5 LEAD CASE 463B



UDFN8, 2x2, 0.5P CASE 517AW



SOIC-8 NB CASE 751-07



SOIC-14 NB CASE 751A-03



TSSOP-14 WB CASE 948G

XX = Specific Device Code A = Assembly Location

Y = Year
W = Work Week
M = Date Code
G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

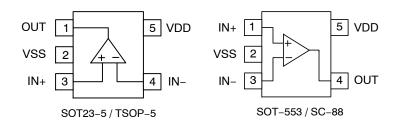
Temperature	Channels	Package	Device Part Number	Marking	Shipping <sup>†</sup>
Industrial and Commerc	ial				
-40°C to 125°C	Single	TSOP-5	NCS20231SN2T1G	AAC	3000 / Tape & Reel
		SC-88	NCS20231SQ3T2G	AAG	3000 / Tape & Reel
		SOT-553	NCS20231XV53T2G	AC	4000 / Tape & Reel
	Dual	SOIC-8	NCS20232DR2G*	N232	2500 / Tape & Reel
		UDFN-8	NCS20232MUTBG*	DGA	3000 / Tape & Reel
	Quad	SOIC-14	NCS20234DR2G*	234G	2500 / Tape & Reel
		TSSOP-14	NCS20234DTBR2G*	N234	2500 / Tape & Reel
Automotive Qualified, G	rade 1		<u> </u>		
-40°C to 150°C	Single	TSOP-5	NCV20231SN2T1G	AAC	3000 / Tape & Reel
		SC-88	NCV20231SQ3T2G	AAG	3000 / Tape & Reel
		SOT-553	NCV20231XV53T2G	AC	4000 / Tape & Reel
	Dual	SOIC-8	NCV20232DR2G*	N232	2500 / Tape & Reel
	Quad	SOIC-14	NCV20234DR2G*	234G	2500 / Tape & Reel
		TSSOP-14	NCV20234DTBR2G*	N234	2500 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

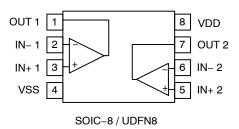
<sup>\*</sup>In Development. Contact local sales office for more information.

#### **PIN CONNECTIONS**

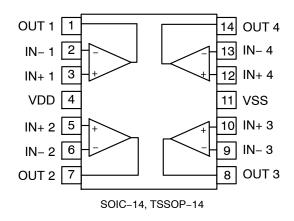
#### Single Channel



#### **Dual Channel**



#### **Quad Channel**



#### **ABSOLUTE MAXIMUM RATINGS** (Note 1)

Parameter	Symbol	Value	Unit
Supply Voltage Range (V <sub>DD</sub> - V <sub>SS</sub> )	V <sub>S</sub>	-0.3 to 40	V
Input Common-Mode Voltage	V <sub>CM</sub>	V <sub>SS</sub> – 0.2 to V <sub>DD</sub> + 0.2	V
Differential Input Voltage	V <sub>ID</sub>	±V <sub>S</sub>	V
Maximum Input Current	I <sub>I</sub>	±10	mA
Maximum Output Current	I <sub>O</sub>	±100	mA
Continuous Total Power Dissipation	P <sub>D</sub>	200	mW
Maximum Junction Temperature	T <sub>J(max)</sub>	150	°C
Storage Temperature Range	T <sub>STG</sub>	-65 to 150	°C
ESD Capability, Human Body Model (Note 2)	НВМ	±2000	V
ESD Capability, Charge Device Model (Note 2)	CDM	±1000	V
Moisture Sensitivity Level	MSL	Level 1	
Lead Temperature Soldering Reflow (SMD Styles Only), Pb-Free Versions (Note 3)	T <sub>SLD</sub>	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Refer to ELECTRICAL CHĂRACTERISTICS and APPLICATION INFORMATION for Safe Operating Area
- This device series incorporates ESD protection and is tested by the following methods:
   ESD Human Body Model tested per JEDEC standard JS-001-2017 (AEC-Q100-002)
   ESD Charged Device Model tested per JEDEC standard JS-002-2014 (AEC-Q100-011)
- 3. For information, please refer to our Soldering and Mounting Techniques Reference Manual, SOLDERRM/D

#### THERMAL CHARACTERISTICS (Note 4)

Package	θ <sub>JA</sub> Junction–to–Ambient Thermal Resistance	Ψ <sub>JT</sub> Junction–to–Case Top Thermal Characteristic	Ψ <sub>JB</sub> Junction–to–Board Thermal Characteristic	Unit
TSOP-5 / SOT23-5	254	78	150	°C/W
SC-88A / SC-70-5 / SOT-353	902	70	810	°C/W
SOT-553	238	14	134	°C/W
SOIC-8	186	32	116	°C/W
UDFN-8	128	10	47	°C/W
SOIC-14	133	7	85	°C/W
TSSOP-14	130	3	73	°C/W

<sup>4.</sup> Thermal parameters are based on a 2s2p board following JESD51-7 (JEDEC)

#### **RECOMMENDED OPERATING RANGES** (Note 5)

Parameter	Symbol	Min	Max	Unit
Supply Voltage (V <sub>DD</sub> – V <sub>SS</sub> )	V <sub>S</sub>	2.7	36	V
Differential Input Voltage (V <sub>IN+</sub> - V <sub>IN-</sub> )	V <sub>ID</sub>		±5 (Note 6)	V
Input Common-Mode Range (Note 7)	V <sub>CM</sub>	V <sub>SS</sub> – 0.1	V <sub>DD</sub> – 2 V	V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

- 5. Refer to ELECTRICAL CHARACTERISTICS and APPLICATION INFORMATION for Safe Operating Area
- The differential voltage may not exceed the supply voltage, ±V<sub>S</sub>. For supplies greater than V<sub>S</sub> = 5 V, differential voltages up to ±V<sub>S</sub> will consume more input current. See APPLICATION INFORMATION.
- 7. The specified input common mode range yields the best performance. However, the input common mode range is functional up to V<sub>DD</sub> + 0.1 V. See APPLICATION INFORMATION.

**ELECTRICAL CHARACTERISTICS** ( $V_S$  = 2.7 V to 36 V) At  $T_A$  = +25°C,  $R_L$  = 10 kΩ connected to midsupply,  $V_{CM}$  =  $V_{OUT}$  = midsupply, unless otherwise noted. **Boldface** limits apply over the specified temperature range, guaranteed by characterization and/or design.

Parameter	Symbol	Conditions	Supply Voltage (V)	Temp (°C)	Min	Тур	Max	Unit
INPUT CHARACTERI	STICS							
Offset Voltage	Vos	V <sub>CM</sub> = mid-supply	2.7, 5, 10, 36	25		±0.3	±0.95	mV
				-40 to 125			±1.2	
				-40 to 150			±1.2	
Offset Voltage Drift	dV <sub>OS</sub> /dT	V <sub>CM</sub> = mid-supply	2.7, 5, 10, 36	-40 to 125		±0.5	±2	μV/°C
over Temperature				-40 to 150		±0.5	± <b>5</b>	
Input Bias Current	I <sub>IB</sub>		2.7, 5, 10, 36	25		±5	±60	pА
(Note 8)				-40 to 125			±3000	
				150		±10000		
Input Offset Current	I <sub>OS</sub>		2.7	25		±0.5	±60	pА
(Note 8)				-40 to 125			±500	
				-40 to 150			±2000	
			5, 10	25		±0.5	±60	
				-40 to 125			±800	
				-40 to 150			±2500	
			36	25		±0.5	±60	pА
				-40 to 125			±2000	
				-40 to 150			±2500	
Channel Separation		NCS20232, NCS20234	2.7, 5, 10, 36	25		130		dB
Input Capacitance	C <sub>IN</sub>	IN+	2.7, 36	25		1		pF
		IN-	2.7, 36	25		6		
Common Mode	CMRR	V <sub>CM</sub> = V <sub>SS</sub> - 0.1 V to	2.7	25	80	98		dB
Rejection Ratio		V <sub>DD</sub> – 2 V		-40 to 125	75			
				-40 to 150	69			
			5	25	90	105		
			(Note 8)	-40 to 125	85			
				-40 to 150	80			
			10	25	100	117		
			(Note 8)	-40 to 125	100			
				-40 to 150	94			
			36	25	110	122		
				-40 to 125	110			
				-40 to 150	107			
		V <sub>CM</sub> = V <sub>SS</sub> + 1.8 V to V <sub>DD</sub> - 2.4 V	36	25	117 (Note 8)	125		dB
EMI Rejection Ratio	EMIRR		2.7, 36	25		See Figure 29		dB

<sup>8.</sup> Guaranteed by design and/or characterization.

## **ELECTRICAL CHARACTERISTICS** ( $V_S = 2.7 \text{ V to } 36 \text{ V}$ ) (continued)

At  $T_A = +25^{\circ}C$ ,  $R_L = 10 \text{ k}\Omega$  connected to midsupply,  $V_{CM} = V_{OUT} =$  midsupply, unless otherwise noted. **Boldface** limits apply over the specified temperature range, guaranteed by characterization and/or design.

Parameter	Symbol	Conditions	Supply Voltage (V)	Temp (°C)	Min	Тур	Max	Unit
OUTPUT CHARACTE	ERISTICS		•			'		
Open Loop Voltage	A <sub>VOL</sub>	V <sub>CM</sub> = mid-supply	2.7	25	100	115		dB
Gain				-40 to 125	90			
				-40 to 150	90			
			5	25	120	135		
			(Note 9)	-40 to 125	115			
				-40 to 150	115			
			10	25	130	145		
			(Note 9)	-40 to 125	120			
				-40 to 150	120			
			36	25	135	154		
				-40 to 125	130			
				-40 to 150	130			
Open Loop Output Impedance	Z <sub>OUT</sub>					See Figure 28		Ω
High Level Output	V <sub>DD</sub> -V <sub>OH</sub>	$R_L = 10 \text{ k}\Omega$	2.7, 5, 10, 36	25		60	80	mV
√oltage Swing from √ <sub>DD</sub>				-40 to 125			120	
.00				-40 to 150			150	
		R <sub>L</sub> = 1 mA	2.7, 5, 10, 36	25		40	60	-
				-40 to 125			80	
				-40 to 150			100	
		R <sub>L</sub> = 5 mA	10	25		165	200	
				-40 to 125			350	1
				-40 to 150			400	
Low Level Output	V <sub>OL</sub> -V <sub>SS</sub>	R <sub>L</sub> = 10 kΩ	2.7, 5, 10	25		16	30	mV
Voltage Swing from V <sub>SS</sub>				-40 to 125			50	
<b>v</b> 55				-40 to 150			50	
			36	25		55	80	
				-40 to 125			250	
				-40 to 150			120	
		R <sub>L</sub> = 1 mA	2.7, 5, 10, 36	25		35	50	
		_		-40 to 125			80	
				-40 to 150			80	
		R <sub>L</sub> = 5 mA	10	25		150	170	
		_		-40 to 125			300	-
				-40 to 150			300	
Output Current Capability	I <sub>OUT</sub>	Output to V <sub>DD</sub> rail, sinking current	2.7, 5, 10, 36	25		28		mA
		Output to V <sub>SS</sub> rail, sourcing current	2.7, 5, 10, 36	25		28		
Capacitive Load Drive	C <sub>L</sub>	Phase margin = 35°	2.7 to 36	25		140		pF

<sup>9.</sup> Guaranteed by design and/or characterization.

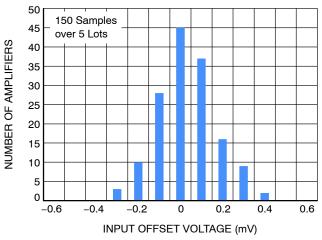
**ELECTRICAL CHARACTERISTICS** ( $V_S = 2.7 \text{ V to } 36 \text{ V}$ ) (continued) At  $T_A = +25^{\circ}\text{C}$ ,  $R_L = 10 \text{ k}\Omega$  connected to midsupply,  $V_{CM} = V_{OUT} =$  midsupply, unless otherwise noted. **Boldface** limits apply over the specified temperature range, guaranteed by characterization and/or design.

Parameter	Symbol	Conditions	Supply Voltage (V)	Temp (°C)	Min	Тур	Max	Unit
DYNAMIC PERFORM	ANCE							•
Gain Bandwidth Product	GWBP	C <sub>L</sub> = 25 pF	2.7, 5, 10, 36	25		3		MHz
Gain Margin	A <sub>m</sub>	C <sub>L</sub> = 25 pF	2.7, 5, 10, 36	25		16		dB
Phase Margin	$\Phi_{m}$	C <sub>L</sub> = 25 pF	2.7, 5, 10, 36	25		60		٥
Slew Rate	SR	Unity gain, $R_L = 2 \text{ k}\Omega$	2.7, 5, 10, 36	25		4		V/μs
Settling Time to	ts	V <sub>IN</sub> = 1 V step	2.7	25		7		μs
0.1 %		V <sub>IN</sub> = 3 V step	5	25		7		
		V <sub>IN</sub> = 8 V step	10	25		7		
		V <sub>IN</sub> = 10 V step	36	25		6		
Settling Time to	t <sub>s</sub>	V <sub>IN</sub> = 1 V step	2.7	25		20		μs
0.01 %		V <sub>IN</sub> = 3 V step	5	25		10		
		V <sub>IN</sub> = 8 V step	10	25		9		
		V <sub>IN</sub> = 10 V step	36	25		9		
NOISE PERFORMAN	CE							
Total Harmonic Distortion + Noise	THD+ N	$V_{IN} = 0.5 V_{pp},$ f = 1 kHz, A <sub>V</sub> = 1	2.7	25		0.009		%
		$V_{IN} = 2.5 V_{pp},$ f = 1 kHz, A <sub>V</sub> = 1	5	25		0.0004		
		V <sub>IN</sub> = 7.5 V <sub>pp</sub> , f = 1 kHz, A <sub>V</sub> = 1	10	25		0.0002		
		$V_{IN} = 28.5 V_{pp},$ f = 1 kHz, A <sub>V</sub> = 1	36	25		0.0002		
Voltage Noise		f = 1 kHz	2.7, 5, 10, 36	25		20		nV/√Hz
Density	e <sub>n</sub>	f = 10 kHz				20		
Current Noise Density	i <sub>n</sub>	f = 1 kHz	2.7, 5, 10, 36	25		30		fA/√Hz
Voltage Noise, Peak to Peak	e <sub>pp</sub>	f <sub>IN</sub> = 0.1 Hz to 10 Hz	2.7, 5, 10, 36	25		700		nV <sub>pp</sub>
POWER SUPPLY								
Power Supply	PSRR	Vs = 2.7 V to 36 V	2.7, 36	25	125	138		dB
Rejection Ratio			,	-40 to 125	120			
				-40 to 150	120			
Quiescent Current	IQ	No load, per channel	2.7, 5	25		0.37	0.595	mA
	~			-40 to 125			0.650	
				-40 to 150			0.7	
			10	25		0.375	0.595	1
				-40 to 125			0.650	
				-40 to 150			0.75	_
			36	25		0.41	0.595	1
				-40 to 125			0.650	
	I	I			l			_

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

#### TYPICAL CHARACTERISTICS

Typical Performance at  $T_A = 25^{\circ}C$ , VCM = mid-supply,  $C_L = 20$  pF,  $R_L = 10$  k $\Omega$  to mid-supply, unless otherwise noted



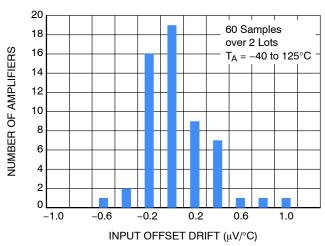


Figure 2. Input Offset Voltage Drift Distribution



Figure 1. Input Offset Voltage Distribution

INPUT OFFSET VOLTAGE (mV) 2 T<sub>A</sub> = 150°C 0 -2 -4 -6 -8 -10 0.5 1.5 2.5 3.5 4.5 5.5 -0.5

COMMON MODE VOLTAGE (V) Figure 3. Input Offset Voltage vs. Common

Mode Voltage

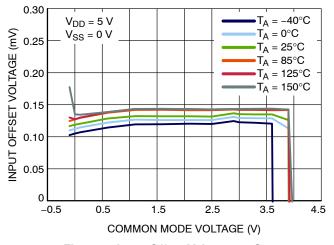


Figure 4. Input Offset Voltage vs. Common Mode Voltage, Performance Region

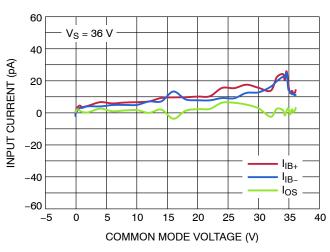


Figure 5. Input Current vs. Common Mode Voltage

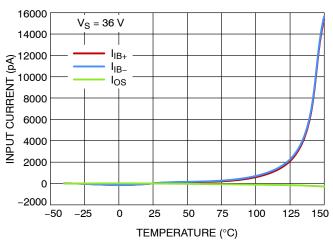
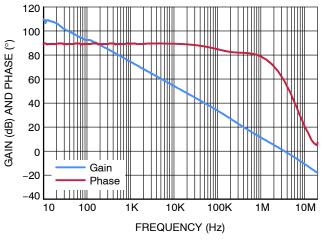


Figure 6. Input Current vs. Temperature

#### **TYPICAL CHARACTERISTICS**

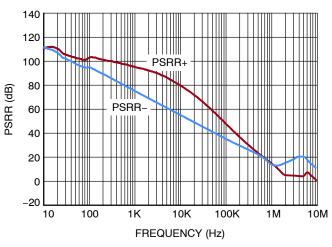
Typical Performance at  $T_A = 25^{\circ}C$ , VCM = mid-supply,  $C_L = 20$  pF,  $R_L = 10$  k $\Omega$  to mid-supply, unless otherwise noted



120 100 80 CMRR (dB) 60 40 20 0 -20 100 10K 100K 10M 10 1K 1M FREQUENCY (Hz)

Figure 7. Open Loop Gain and Phase vs. Frequency

Figure 8. CMRR vs. Frequency



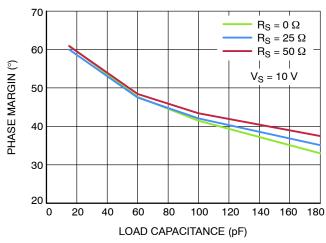
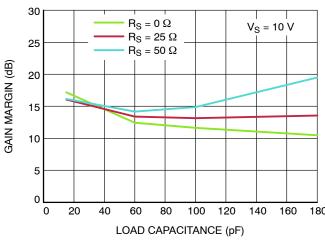


Figure 9. PSRR vs. Frequency

Figure 10. Phase Margin vs. Capacitive Load



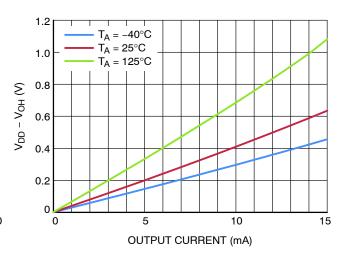
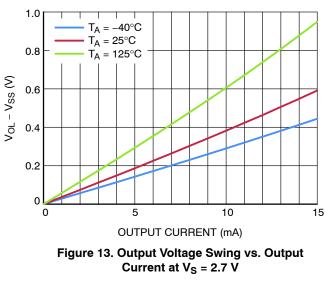


Figure 11. Gain Margin vs. Capacitive Load

Figure 12. Output Voltage Swing High vs. Output Current at  $V_S = 2.7 \text{ V}$ 

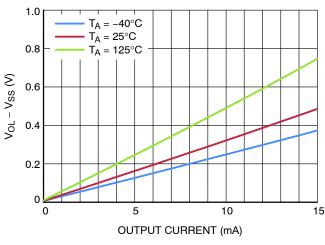
#### **TYPICAL CHARACTERISTICS**

Typical Performance at  $T_A = 25^{\circ}C$ , VCM = mid-supply,  $C_L = 20$  pF,  $R_L = 10$  k $\Omega$  to mid-supply, unless otherwise noted



1.2  $T_{A} = -40^{\circ}C$   $T_{A} = 25^{\circ}C$   $T_{A} = 125^{\circ}C$   $T_{A} = 125^{\circ}C$ 

Figure 14. Output Voltage Swing vs. Output Current at  $V_S = 36 \text{ V}$ 



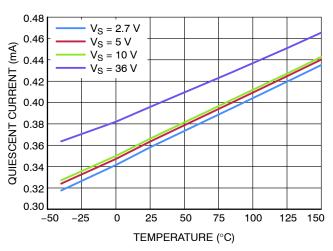
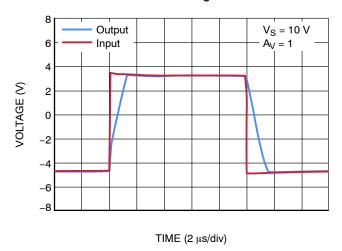


Figure 15. Output Voltage Swing vs. Output Current at  $V_S = 36 \text{ V}$ 

Figure 16. Quiescent Current vs. Temperature



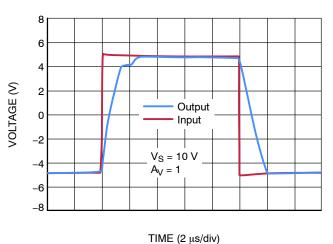


Figure 17. Large Signal Step Response

Figure 18. Large Signal Step Response

#### **TYPICAL CHARACTERISTICS**

Typical Performance at  $T_A$  = 25°C, VCM = mid-supply,  $C_L$  = 20 pF,  $R_L$  = 10 k $\Omega$  to mid-supply, unless otherwise noted

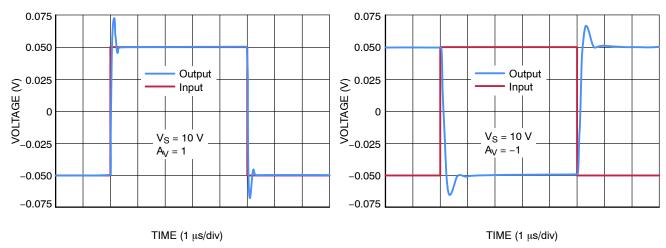


Figure 19. Small Signal Step Response

Figure 20. Small Signal Step Response

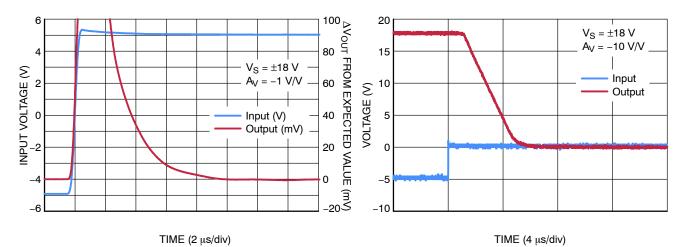


Figure 21. Settling Time

Figure 22. Output Overload Recovery Response

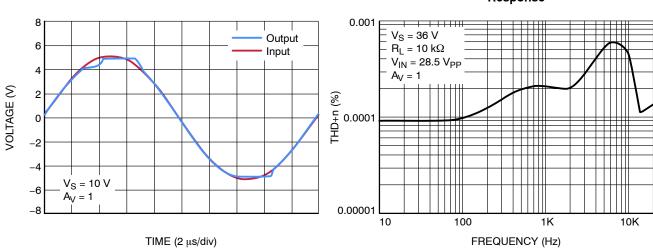


Figure 23. No Phase Reversal

Figure 24. THD+n vs. Frequency

#### **TYPICAL CHARACTERISTICS**

Typical Performance at  $T_A = 25^{\circ}C$ , VCM = mid-supply,  $C_L = 20$  pF,  $R_L = 10$  k $\Omega$  to mid-supply, unless otherwise noted

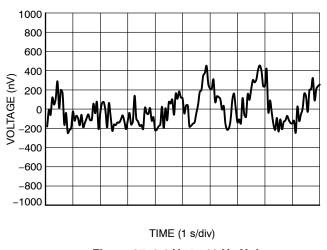


Figure 25. 0.1 Hz to 10 Hz Noise

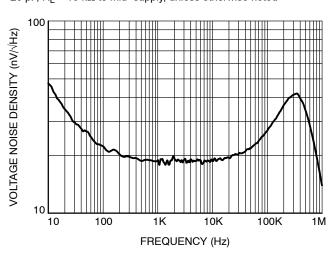


Figure 26. Voltage Noise Density vs. Frequency

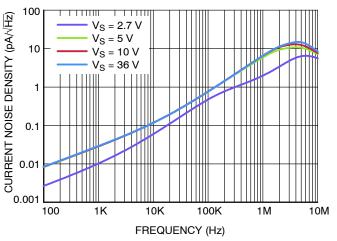


Figure 27. Current Noise Density vs. Frequency

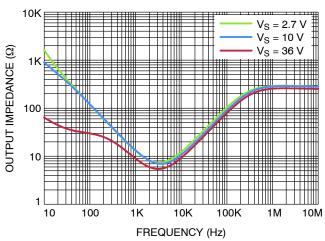


Figure 28. Open Loop Output Impedance vs. Frequency

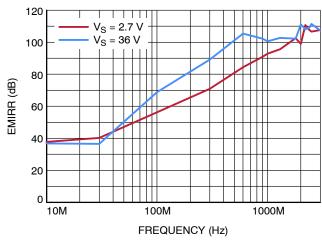


Figure 29. EMIRR vs. Frequency

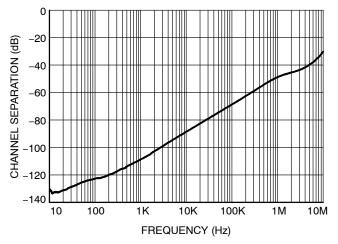


Figure 30. Channel Separation vs. Frequency

#### APPLICATION INFORMATION

#### Input and ESD Structure

The NCS20231 series amplifiers have back–to–back Zener diodes, which allow for normal operation with the differential voltage up to  $\pm 5$  V. Differential voltages beyond this are permitted, up to  $\pm V_S$ , but increased input leakage

current should be expected. Internal current limiting resistors in series with the input pins limit the current to  $\pm 10$  mA in scenarios where the differential voltage is as high as  $\pm 36$  V.

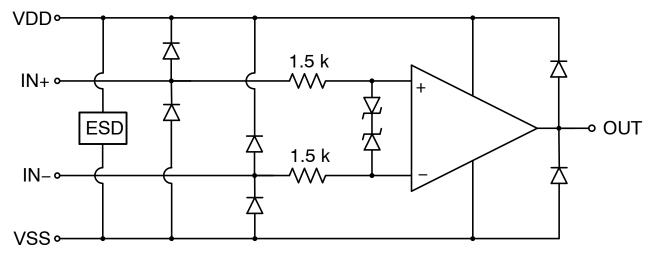


Figure 31. Representative Schematic of the Op Amp

Each input pin is diode clamped to the rails. In case of an input overvoltage, input currents must be limited to within  $\pm 10$  mA to prevent excessive current from damaging the part.

#### Rail-to-Rail Performance

The functional common mode input voltage spans 100 mV beyond the rails. High precision performance, as

shown throughout the ELECTRICAL CHARACTERISTICS table, is achieved in the  $V_{SS}-0.1~V$  to  $V_{DD}-2~V$  common mode voltage range. The input common mode extends further up to  $V_{DD}+0.1~V$  to ensure functionality near the upper rail, though without precision performance in that region. The typical performance within the  $V_{DD}-2~V$  to  $V_{DD}+0.1~V$  range is shown in the table below.

Parameter	Symbol	Conditions	Тур	Units
Input Offset Voltage	Vos	$V_{CM} = V_{DD} - 0.5 V$	±9	mV
Input Offset Voltage over Temperature	dV <sub>OS</sub> /dT		±24	μV/°C
Common Mode Rejection Ratio	CMRR	$V_{CM} = V_{DD} - 0.5 \text{ V to } V_{DD} + 0.1 \text{ V}$	75	dB
Open Loop Voltage Gain	A <sub>VOL</sub>	$V_{CM} = V_{DD} - 0.5 V$	90	dB
Gain Bandwidth Product	GBWP	$V_{CM} = V_{DD} - 0.5 \text{ V}, C_L = 25 \text{ pF}$	2.5	MHz
Slew Rate	SR	Unity gain, $V_{CM} = V_{DD} - 1 V \text{ to } V_{DD} - 0.2 V$	1.2	V/μs
Voltage Noise Density	e <sub>n</sub>	f = 1 kHz	1000	nV/√Hz

The NCS2023x does not exhibit output phase reversal. Phase reversal occurs in some amplifiers when the input voltage exceeds the recommended input common mode voltage range, causing the output to flip to the opposite rail.

Instead, when the input common mode voltage range is exceeded on the NCS2023x, the output becomes clipped at the output, limited by the output voltage swing.





#### SC-88A (SC-70-5/SOT-353) CASE 419A-02 ISSUE M

**DATE 11 APR 2023** 

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. 419A-01 DBSOLETE, NEW STANDARD 419A-02
- 4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH,
  PROTRUSIONS, OR GATE BURRS.MOLD FLASH, PROTRUSIONS,
  OR GATE BURRS SHALL NOT EXCEED 0.1016MM PER SIDE.

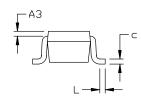
DIM	MILLIMETERS					
ابالط	MIN.	N□M.	MAX.			
Α	0.80	0.95	1.10			
A1			0.10			
A3	0,20 REF					
b	0.10	0.20	0.30			
С	0.10		0.25			
D	1.80	2.00	2.20			
Е	2.00	2.10	2.20			
E1	1.15	1.25	1.35			
е	0.65 BSC					
L	0.10	0.15	0.30			

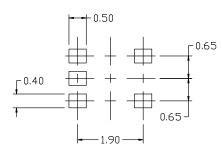
## 



5X b

→ 0.2 M B M





## RECOMMENDED MOUNTING FOOTPRINT

\* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

#### GENERIC MARKING DIAGRAM\*



\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

XXX = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

STYLE -	1:
PIN 1.	BASE
2.	EMITTER
3.	BASE
4.	COLLECTOR
5.	COLLECTOR

STYLE 2:
PIN 1. ANODE
2. EMITTER
3. BASE
4. COLLECTOR
5. CATHODE

STYLE 3: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. CATHODE 1 STYLE 4: PIN 1. SOURCE 1 2. DRAIN 1/2 3. SOURCE 1 4. GATE 1 5. GATE 2

STYLE 5:
PIN 1. CATHODE
2. COMMON ANODE
3. CATHODE 2
4. CATHODE 3
5. CATHODE 4

STYLE 6: PIN 1. EMITTER 2 2. BASE 2 3. EMITTER 1 4. COLLECTOR STYLE 7: PIN 1. BASE 2. EMITTER 3. BASE 4. COLLECTOR 5. COLLECTOR

STYLE 8: PIN 1. CATHODE 2. COLLECTOR 3. N/C 4. BASE

5. EMITTER

STYLE 9: PIN 1. ANODE 2. CATHODE 3. ANODE 4. ANODE 5. ANODE Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

#### **DOCUMENT NUMBER:**

98ASB42984B

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**DESCRIPTION:** 

5. COLLECTOR 2/BASE 1

SC-88A (SC-70-5/SOT-353)

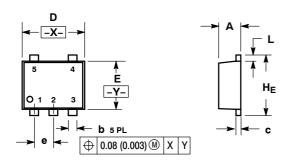
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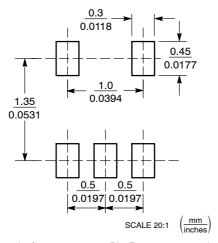


SOT-553, 5 LEAD CASE 463B ISSUE C

**DATE 20 MAR 2013** 



#### **RECOMMENDED SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### NOTES:

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETERS

  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH
  THICKNESS: MINIMUM LEAD THICKNESS IS THE MINIMUM
  THICKNESS OF BASE MATERIAL.

	М	ILLIMETE	RS	INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.50	0.55	0.60	0.020	0.022	0.024	
b	0.17	0.22	0.27	0.007	0.009	0.011	
С	0.08	0.13	0.18	0.003	0.005	0.007	
D	1.55	1.60	1.65	0.061	0.063	0.065	
E	1.15	1.20	1.25	0.045	0.047	0.049	
е		0.50 BSC			0.020 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012	
He	1.55	1.60	1.65	0.061	0.063	0.065	

#### **GENERIC MARKING DIAGRAM\***



XX = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. CATHODE	PIN 1. ANODE 1	PIN 1. SOURCE 1	PIN 1. ANODE
2. EMITTER	2. COMMON ANODE	2. N/C	2. DRAIN 1/2	2. EMITTER
3. BASE	<ol><li>CATHODE 2</li></ol>	3. ANODE 2	3. SOURCE 1	3. BASE
4. COLLECTOR	<ol><li>CATHODE 3</li></ol>	<ol><li>CATHODE 2</li></ol>	4. GATE 1	4. COLLECTOR
<ol><li>COLLECTOR</li></ol>	<ol><li>CATHODE 4</li></ol>	<ol><li>CATHODE 1</li></ol>	5. GATE 2	<ol><li>CATHODE</li></ol>
STYLE 6:	STYLE 7:	STYLE 8:	STYLE 9:	
PIN 1. EMITTER 2	PIN 1. BASE	PIN 1. CATHODE	PIN 1. ANODE	
2. BASE 2	2. EMITTER	2. COLLECTOR	2. CATHODE	
3. EMITTER 1	3. BASE	3. N/C	3. ANODE	
4. COLLECTOR 1	4. COLLECTOR	4. BASE	4. ANODE	
<ol><li>COLLECTOR 2/BASE 1</li></ol>	5. COLLECTOR	5. EMITTER	5. ANODE	

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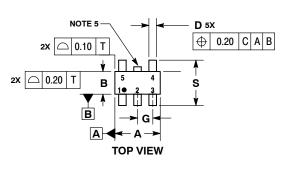
ISSUE	REVISION	DATE
Α	ADDED STYLES 3-9. REQ. BY D. BARLOW	11 NOV 2003
В	ADDED NOMINAL VALUES AND UPDATED GENERIC MARKING DIAGRAM. REQ. BY HONG XIAO	27 MAY 2005
С	UPDATED DIMENSIONS D, E, AND HE. REQ. BY J. LETTERMAN.	20 MAR 2013

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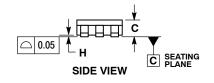


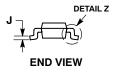
TSOP-5 **CASE 483 ISSUE N** 

**DATE 12 AUG 2020** 







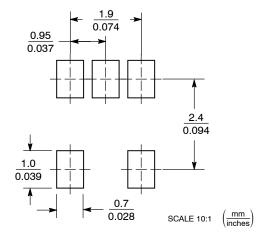


#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME
- CONTROLLING DIMENSION: MILLIMETERS.
  MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH
  THICKNESS. MINIMUM LEAD THICKNESS IS THE
  MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSION A. OPTIONAL CONSTRUCTION: AN ADDITIONAL
- TRIMMED LEAD IS ALLOWED IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY.

	MILLIMETERS		
DIM	MIN	MAX	
Α	2.85	3.15	
В	1.35	1.65	
С	0.90	1.10	
D	0.25	0.50	
G	0.95	BSC	
Н	0.01	0.10	
J	0.10	0.26	
K	0.20	0.60	
М	0 °	10 °	
S	2 50	3.00	

#### **SOLDERING FOOTPRINT\***



<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **GENERIC MARKING DIAGRAM\***





XXX = Specific Device Code XXX = Specific Device Code

= Assembly Location = Date Code

= Year = Pb-Free Package

= Work Week W

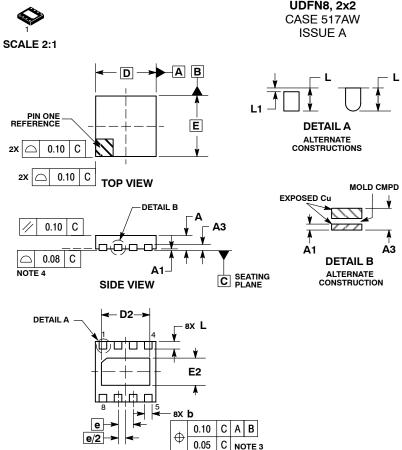
= Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

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## **UDFN8, 2x2**

**DATE 13 NOV 2015** 

#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS. DIMENSION 6 APPLIES TO PLATED TERMI-NALS AND IS MEASURED BETWEEN 0.15 AND 0.30 MM FROM THE TERMINAL TIP.
- AND 0.30 MM FHOM THE TEHMINAL TIP.
  COPLANARITY APPLIES TO THE EXPOSED
  PAD AS WELL AS THE TERMINALS.
  FOR DEVICE OPN CONTAINING W OPTION,
  DETAIL B ALTERNATE CONSTRUCTION IS
  NOT APPLICABLE.

	MILLIMETERS		
DIM	MIN	MAX	
Α	0.45	0.55	
<b>A</b> 1	0.00	0.05	
А3	0.13	REF	
b	0.18	0.30	
D	2.00	BSC	
D2	1.50	1.70	
Е	2.00	BSC	
E2	0.80	1.00	
е	0.50 BSC		
L	0.20	0.45	
11		0.15	

#### **GENERIC MARKING DIAGRAM\***



XX = Specific Device Code

= Date Code

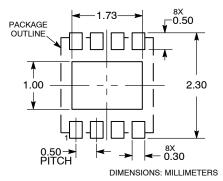
= Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " •", may or may not be present.

#### **RECOMMENDED SOLDERING FOOTPRINT\***

**BOTTOM VIEW** 



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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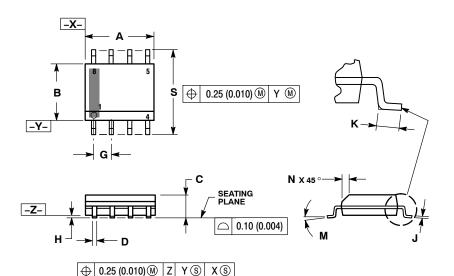
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SOIC-8 NB CASE 751-07 **ISSUE AK** 

**DATE 16 FEB 2011** 



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
  CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.80	5.00	0.189	0.197
В	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
Н	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
М	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

XXXXXX

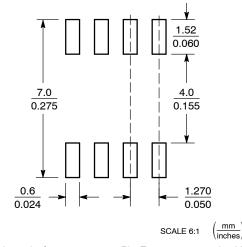
AYWW

Discrete

Ŧ  $\mathbb{H}$  AYWW

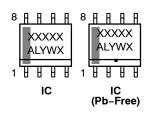
**Discrete** (Pb-Free)

#### **SOLDERING FOOTPRINT\***



<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### **GENERIC MARKING DIAGRAM\***



XXXXX = Specific Device Code = Assembly Location = Wafer Lot = Year W

XXXXXX = Specific Device Code = Assembly Location Α = Year ww = Work Week = Work Week = Pb-Free Package = Pb-Free Package

> \*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

#### **STYLES ON PAGE 2**

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DESCRIPTION:	SOIC-8 NB		PAGE 1 OF 2

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#### SOIC-8 NB CASE 751-07 ISSUE AK

#### **DATE 16 FEB 2011**

			D/ (I E TO I ED E
STYLE 1: PIN 1. EMITTER 2. COLLECTOR 3. COLLECTOR 4. EMITTER 5. EMITTER 6. BASE 7. BASE 8. EMITTER	STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 5. BASE, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1 STYLE 6:	STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1 STYLE 7:	
PIN 1. DRAIN 2. DRAIN 3. DRAIN 4. DRAIN 5. GATE 6. GATE 7. SOURCE 8. SOURCE	PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE	STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd	PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 8. COLLECTOR, #1
STYLE 9: PIN 1. EMITTER, COMMON 2. COLLECTOR, DIE #1 3. COLLECTOR, DIE #2 4. EMITTER, COMMON 5. EMITTER, COMMON 6. BASE, DIE #2 7. BASE, DIE #1 8. EMITTER, COMMON	STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. BIAS 2 7. INPUT 8. GROUND	STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1	STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN	STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN	7. DHAIN 1 8. DRAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON	STYLE 16:  PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1
STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC	STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE	STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1	STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3. CATHODE 3 4. CATHODE 4 5. CATHODE 5 6. COMMON ANODE 7. COMMON ANODE 8. CATHODE 6	STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND	STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT	STYLE 24: PIN 1. BASE 2. EMITTER 3. COLLECTOR/ANODE 4. COLLECTOR/ANODE 5. CATHODE 6. CATHODE 7. COLLECTOR/ANODE 8. COLLECTOR/ANODE
STYLE 25: PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT	STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN
STYLE 29: PIN 1. BASE, DIE #1 2. EMITTER, #1 3. BASE, #2 4. EMITTER, #2 5. COLLECTOR, #2 6. COLLECTOR, #2 7. COLLECTOR, #1 8. COLLECTOR, #1	STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		

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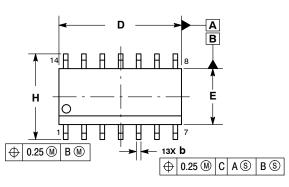


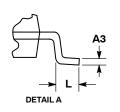


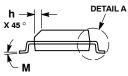
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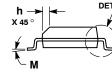
SOIC-14 NB CASE 751A-03 ISSUE L

**DATE 03 FEB 2016** 





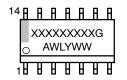




- NOTES:
  1. DIMENSIONING AND TOLERANCING PER
  - ASME Y14.5M, 1994.
    CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT
- MAXIMUM MATERIAL CONDITION.
  DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
- MAXIMUM MOLD PROTRUSION 0.15 PER SIDE

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
АЗ	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
Е	3.80	4.00	0.150	0.157
е	1.27	BSC	0.050 BSC	
Н	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
Ĺ	0.40	1.25	0.016	0.049
М	0 °	7°	0 °	7°

#### **GENERIC MARKING DIAGRAM\***

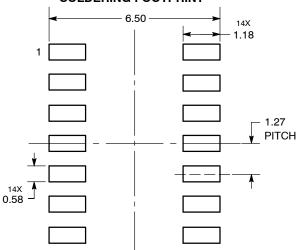


XXXXX = Specific Device Code Α = Assembly Location

WL = Wafer Lot Υ = Year WW = Work Week = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

### **SOLDERING FOOTPRINT\***



DIMENSIONS: MILLIMETERS

C SEATING PLANE

#### **STYLES ON PAGE 2**

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<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### SOIC-14 CASE 751A-03 ISSUE L

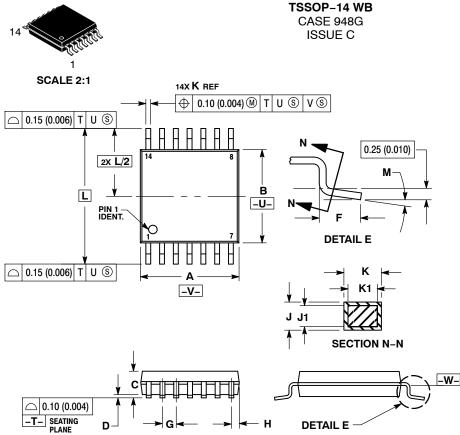
#### DATE 03 FEB 2016

STYLE 1: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. NO CONNECTION 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. NO CONNECTION 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 2: CANCELLED	STYLE 3: PIN 1. NO CONNECTION 2. ANODE 3. ANODE 4. NO CONNECTION 5. ANODE 6. NO CONNECTION 7. ANODE 8. ANODE 9. ANODE 10. NO CONNECTION 11. ANODE 12. ANODE 13. NO CONNECTION 14. COMMON CATHODE	STYLE 4: PIN 1. NO CONNECTION 2. CATHODE 3. CATHODE 4. NO CONNECTION 5. CATHODE 6. NO CONNECTION 7. CATHODE 8. CATHODE 9. CATHODE 10. NO CONNECTION 11. CATHODE 12. CATHODE 13. NO CONNECTION 14. COMMON ANODE
STYLE 5: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. NO CONNECTION 7. COMMON ANODE 8. COMMON CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. ANODE/CATHODE 12. ANODE/CATHODE 13. NO CONNECTION 14. COMMON ANODE	STYLE 6: PIN 1. CATHODE 2. CATHODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE 7. CATHODE 8. ANODE 9. ANODE 10. ANODE 11. ANODE 12. ANODE 13. ANODE 14. ANODE	STYLE 7: PIN 1. ANODE/CATHODE 2. COMMON ANODE 3. COMMON CATHODE 4. ANODE/CATHODE 5. ANODE/CATHODE 6. ANODE/CATHODE 7. ANODE/CATHODE 8. ANODE/CATHODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. COMMON CATHODE 12. COMMON ANODE 13. ANODE/CATHODE 14. ANODE/CATHODE	STYLE 8: PIN 1. COMMON CATHODE 2. ANODE/CATHODE 3. ANODE/CATHODE 4. NO CONNECTION 5. ANODE/CATHODE 6. ANODE/CATHODE 7. COMMON ANODE 8. COMMON ANODE 9. ANODE/CATHODE 10. ANODE/CATHODE 11. NO CONNECTION 12. ANODE/CATHODE 13. ANODE/CATHODE 14. COMMON CATHODE

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**DATE 17 FEB 2016** 

- NOTES.

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETER.

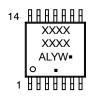
  3. DIMENSION A DOES NOT INCLUDE MOLD
- FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
  DIMENSION B DOES NOT INCLUDE
- INTERLEAD FLASH OR PROTRUSION.
  INTERLEAD FLASH OR PROTRUSION SHALL
- INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

  5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

  6. TERMINAL NUMBERS ARE SHOWN FOR DEFERENCE ONLY.
- REFERENCE ONLY.
  DIMENSION A AND B ARE TO BE
- DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026	BSC
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40	BSC	0.252	BSC
М	o°	8 °	0 °	8 °

#### **GENERIC MARKING DIAGRAM\***



= Assembly Location

= Wafer Lot V = Year

W = Work Week

= Pb-Free Package (Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

SOLDERING FOOTPRINT			
7.	06		
1			
	□ 0.65 PITCH		
<u> </u>	<del></del>		
0.36 14X 1.26	<del></del> ↑		
1 1	DIMENSIONS: MILLIMETERS		

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